

AT24C01/02

I²C-Compatible (2-wire) Serial EEPROM 1-Kbit (128 x 8) or 2-Kbit (256 x 8)

DATASHEET

Features

- Low voltage operation
 - 1.7V (V_{CC} = 1.7V to 3.6V)
- Internally organized 128 x 8 (1K) or 256 x 8 (2K)
- I²C-Compatible (2-wire) serial interface
- Schmitt Triggers, filtered inputs for noise suppression
- Bidirectional data transfer protocol
- Write Protect pin for full array hardware data protection
- 8-byte Page Write mode
 - Partial page writes allowed
- Random and Sequential Read modes
- High reliability

Endurance: 1,000,000 write cycles

Data retention: 100 years

- Green package options (Lead-free/Halide-free/RoHS Compliant)
 - 8-lead SOIC, 8-lead TSSOP, 8-pad UDFN, 8-lead PDIP,⁽¹⁾ 5-lead SOT23, and 8-ball VFBGA
- Die sale options: wafer form and tape and reel available

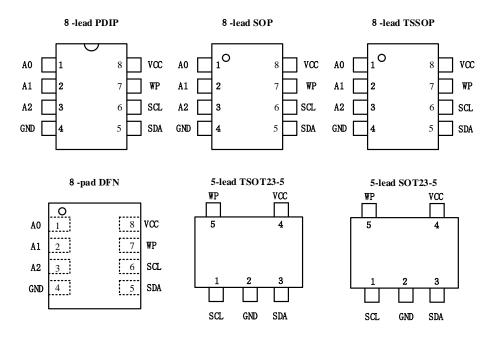
Description

The AT24C01/02 provides 1,024/2,048 bits of Serial Electrically Erasable and Programmable Read-Only Memory (EEPROM) organized as 128/256 words of eight bits each. The device's cascadable feature allows up to eight devices to share a common 2-wire bus. These device are optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. Both devices are available in space-saving 8-lead SOIC, 8-lead TSSOP, 8-pad UDFN, 8-lead PDIP, (1) 5-lead SOT23, and 8-ball VFBGA packages.



AT24C01/02

Pin Configuration



Examples

型号	封装	私印	工作电压	兼容电压
AT24C01D-SSHM-T-TUDI	S0P8	O1DM	1.7to 5.5	
AT24C01C-SSHM-T-TUDI	SOP8	O1CM	1.7to 5.5	3. 6v
CAT24C01WI-GT3-TUDI	SOP8	24C01WI	1.7to 5.5	1. 8v
AT24C01YI-GT3A-TUDI	TSS0P8	24C01Y	1.7to 5.5	
AT24C01D-XHM-T-TUDI	TSS0P8	24C01D	1.7to 5.5	1. 8v
AT24C01C-XHM-T-TUDI	TSS0P8	24C01C	1.7to 5.5	3. 6v
AT24C01B-TH-T-TUDI	TSS0P8	24C01B	1.7to 5.5	2. 7v
AT24C01D-PUM-TUDI	DIP8	24C01D	1.7to 5.5	
AT24C01C-PUM-TUDI	DIP8	24C01C	1.7to 5.5	3. 6v
AT24C01C-STUM-T-TUDI	S0T23-5	24C01C	1.7to 5.5	3. 6v
AT24C01D-STUM-T-TUDI	S0T23-5	24C01D	1.7to 5.5	
AT24C02D-SSHM-T-TUDI	SOP8	O2DM	1.7to 5.5	
AT24C02C-SSHM-T-TUDI	S0P8	02CM	1.7to 5.5	3. 6v
CAT24C02WI-GT3-TUDI	SOP8	24C02WI	1.7to 5.5	1. 8v
CAT24C02YI-GT3A-TUDI	TSS0P8	24C02Y	1.7to 5.5	
AT24C02D-XHM-T-TUDI	TSS0P8	24C02D	1.7to 5.5	1. 8v
AT24C02C-XHM-T-TUDI	TSS0P8	24C02C	1.7to 5.5	3. 6v
AT24C02B-TH-T-TUDI	TSS0P8	24C02B	1.7to 5.5	2. 7v
AT24C02D-PUM-TUDI	DIP8	24C02D	1.7to 5.5	
AT24C02C-PUM-TUDI	DIP8	24C02C	1.7to 5.5	3. 6v
AT24C02C-STUM-T-TUDI	S0T23-5	24C02C	1.7to 5.5	3. 6v
AT24C02D-STUM-T-TUDI	S0T23-5	24C02D	1.7to 5.5	

24C01/24C02 2 / 19



Pin Descriptions

Pin Name	Туре	Functions				
A0-A2	I	Address Inputs				
SDA	I/O	Serial Data				
SCL	I	Serial Clock Input				
WP	I	Write Protect				
GND	Р	Ground				
Vcc	Р	Power Supply				

Table 1

Block Diagram

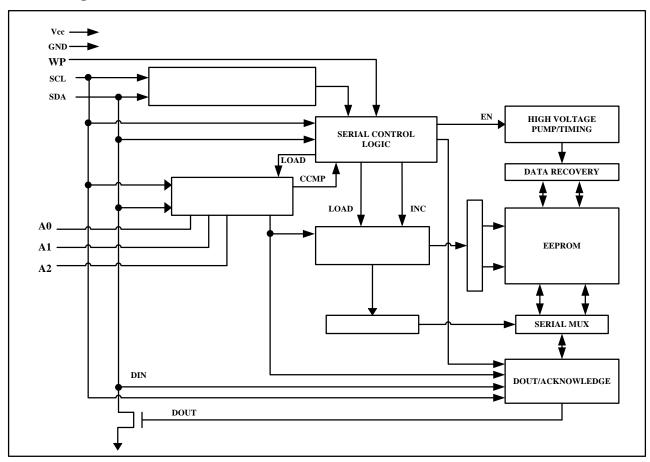


Figure 1

DEVICE/PAGE ADDRESSES (A2, A1 and A0): The A2, A1 and A0 pins are device address inputs that are hard wire for the 24C01/24C02. Eight 2K devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section).

SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open- collector devices.

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

WRITE PROTECT (WP): The 24C01/24C02 has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to ground (GND). When the Write Protection pin is connected to Vcc,

the write protection feature is enabled and operates as shown in the following Table 2.

24C01/24C02 3 / 19



WP Pin Status	24C01/24C02				
At VCC	Full(2K) Array				
At GND	Normal Read/Write Operations				

Table 2

Functional Description

1. Memory Organization

24C01/24C02, 2K SERIAL EEPROM: Internally organized with 16 pages of 16 bytes each, the 2K requires a 8 -bit data word address for random word addressing.

2. Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see **Figure 2**). Data changes during SCL high periods will indicate a start or stop condition as defined below.

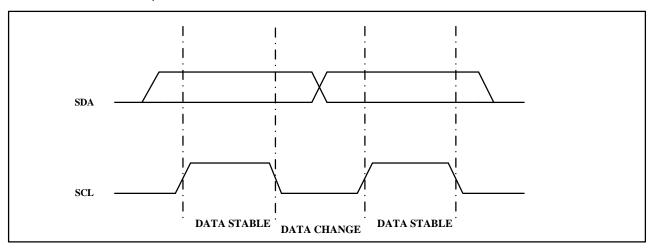


Figure 2. Data Validity

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see **Figure 3**).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (see **Figure 3**).

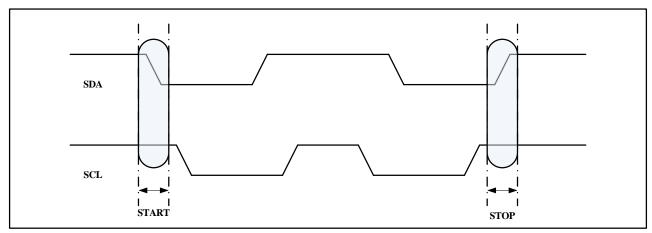


Figure 3. Start and Stop Definition

24C01/24C02 4 / 19

ACKNOWLEDGE: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

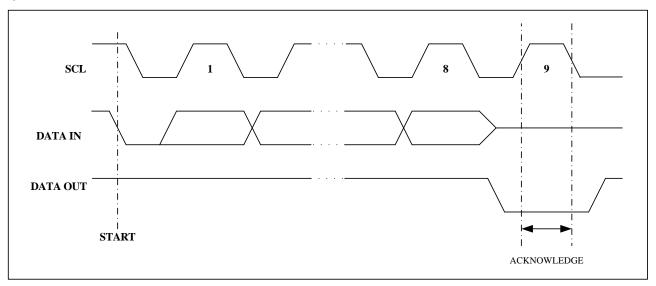


Figure 4. Output Acknowledge

STANDBY MODE: The 24C01/24C02 features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the STOP bit and the completion of any internal operations.

MEMORY RESET: After an interruption in protocol, power loss or system reset, any two-wire part can be reset by following these steps:

- 1. Clock up to 9 cycles.
- 2. Lock SDA high in each cycle while SCL is high.
- 3. Create a start condition.

24C01/24C02 5 / 19

3. Device Addressing

The 2K EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see **Figure 5**)



Figure 5. Device Address

The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices.

The 2K EEPROM uses A2, A1 and A0 device address bits to allow as much as eight devices on the same bus. These 3 bits must be compared to their corresponding hardwired input pins. The A2, A1 and A0 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to a standby state.

DATA SECURITY: The 24C01/24C02 has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at VCC.

4. Write Operations

BYTE WRITE: A write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a "0" and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, tWR, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see **Figure 7**).



Figure 6. ADDRESS

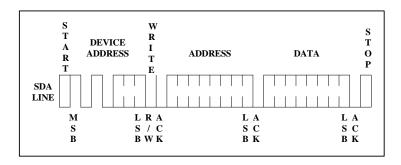


Figure 7. Byte Write

24C01/24C02 6 / 19



PAGE WRITE: The 2K EEPROM is capable of a 16-byte page write. A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see **Figure 8**).

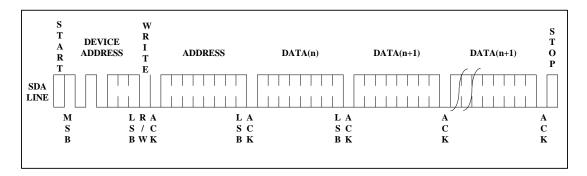


Figure 8. Page Write

The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than sixteen data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.

24C01/24C02 7 / 19



5. Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page. Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see **Figure 9**).

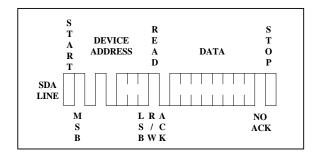


Figure 9. Current Address Read

RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see **Figure 10**)

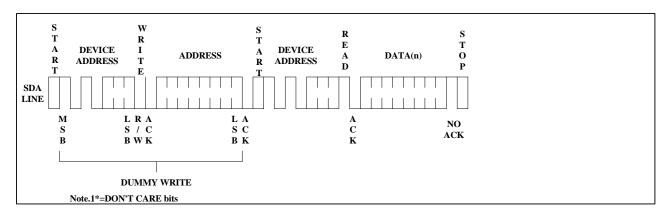


Figure 10. Random Read

24C01/24C02 8 / 19



SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a "0" but does generate a following stop condition (see **Figure 11**).

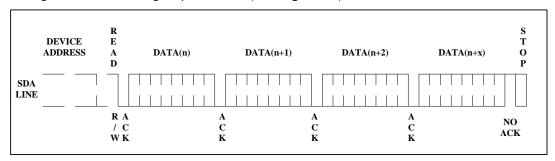


Figure 11. Sequential Read

24C01/24C02 9 / 19



Electrical Characteristics

Absolute Maximum Stress Ratings:

•	DC Supply Voltage	0.3V to +6.5V
•	Input / Output Voltage	GND-0.3V to VCC+0.3V
•	Storage Temperature	65°C to +150°C
•	Electrostatic pulse (Human Body model)	6000V

Comments:

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

DC Electrical Characteristics

24C01/24C02	T _A =-	-40℃ to +85℃		V _{CC} = +1.7V to +5.5V@400kHz					
24C01/24C02 E1	T _A =-40°C to +105°C			$V_{CC} = +2.5V \text{ to } +5.5V @ 1MHz$					
24C01/24C02 E0	T _A =-	T _A =-40°C to +125°C C _L =100 pF							
Parameter		Symbol	Min	Тур	Max	Unit	Condition		
Supply Voltage		V _{CC1}	1.7	-	5.5	V	@400kHz		
Supply Voltage		V _{CC2}	2.5	-	5.5	V	@1MHz		
Supply Current Vcc=5.0\	/ I _R		-	0.14	0.3	mA	READ @ 400kHz		
Supply Current Vcc=5.0\	/	lw	-	0.28	0.5	mA	WRITE @ 400kHz		
Supply Current Vcc=5.0\	/	I _{SB}	-	0.03	0.5	μA	VIN=Vcc or Vss		
Input Leakage Current		lμ	-	0.10	1.0	μA	VIN=VCC or Vss		
Output Leakage Current		ILO	-	0.05	1.0	μA	Vout=Vcc or Vss		
Input Low Level		VIL	-0.3	-	Vcc×0.3	V	Vcc=1.7V to 5.5V		
Input High Level		ViH	Vcc×0.7	7 -	Vcc+0.3	V	Vcc=1.7V to 5.5V		
Output Low Level Vcc=1.7V		V _{OL1}	-	-	0.2	V	I _{OL} =0.15mA		
Output Low Level Vcc=5	.0V	V _{OL2}	-	-	0.4	V	I _{OL} =3.0mA		

Table 3

Pin Capacitance

Applicable over recommended operating range from T_A = 25°C, f_{SCL} = 1.0 MHz, V_{CC} = +2.5V

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Input/Output Capacitance(SDA)	$C_{I/O}$	-	1	8	pF	V _{IO} =0V
Input Capacitance(A0,A1,A2,SCL)	CIN	-	1	6	pF	V _{IN} =0V

Table 4

24C01/24C02 1 0 / 19



AC Electrical Characteristics

Applicable over recommended operating range from (unless otherwise noted):

24C01/24C02	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	V _{CC} = +1.7V to +5.5V@400kHz V _{CC} = +2.5V to +5.5V@1MHz			
24C01/24C02 E1	T _A =-40°C to +105°				
24C01/24C02 E0	T _A =-40°C to +125°C	C∟=100 pF			
Parameter	Symbol	Mir	١.	Max.	Units
Clock Frequency, SCL	fscL	-		1000	kHz
Clock Pulse Width Low	tLow	0.5	5	-	μs
Clock Pulse Width High	t _{HIGH}	0.2	6	-	μs
Noise Suppression Time	tı	-	50		ns
Clock Low to Data Out Valid	t _{AA}	t _{AA} -		0.45	μs
Time the bus must be free before a new transmission can start	t _{BUF}	0.5	5	-	μs
Start Hold Time	thd:sta	0.2	6	-	μs
Start Setup Time	t su:sta	0.2	6	-	μs
Data In Hold Time	thd:dat	0		-	μs
Data In Setup Time	tsu:dat	50)	-	ns
Input Rise Time ^{(1) (2)}	t _R	-		-	ns
Input Fall Time ^{(1) (2)}	t⊧	-		-	ns
Stop Setup Time	tsu:sto	0.2	6	-	μs
Data Out Hold Time	t _{DH}	50)		ns
Write Cycle Time	twR	-		3	ms
5.0V,25°C,Byte Mode ⁽¹⁾	Endurance	1M	1	-	Write Cycle

Table 5

Notes:

1. This parameter is ensured by characterization only.

2. There is no min. or max. values for the input signal rise and fall times. It is however recommended by the I²C specification that the input signal rise and fall times be less than 120 ns when $f_{SCL} < 1$ MHz, more than 20 ns and less than 300 ns when $f_{SCL} < 400$ kHz.

3. AC measurement conditions:

 R_L (connects to V_{CC}): 1.3 $k\Omega$

Input pulse voltages: 0.3 V_{CC} to 0.7 V_{CC}

Input rise and fall time: 50 ns

Input and output timing reference voltages: 0.5 Vcc

The value of R_L should be concerned according to the actual loading on the user's system.

24C01/24C02 12/19



(256×8)Bus Timing

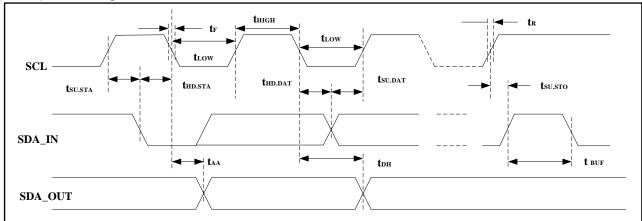


Figure 12. SCL: Serial Clock, SDA: Serial Data I/O

Write Cycle Timing

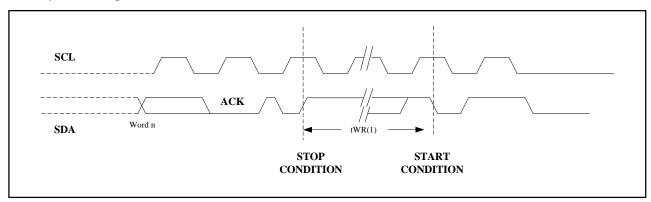
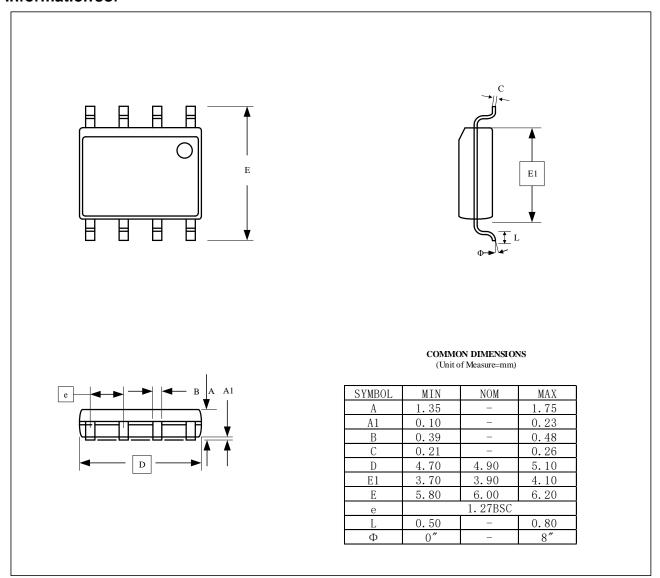


Figure 13. SCL: Serial Clock, SDA: Serial Data I/O

24C01/24C02 13/19



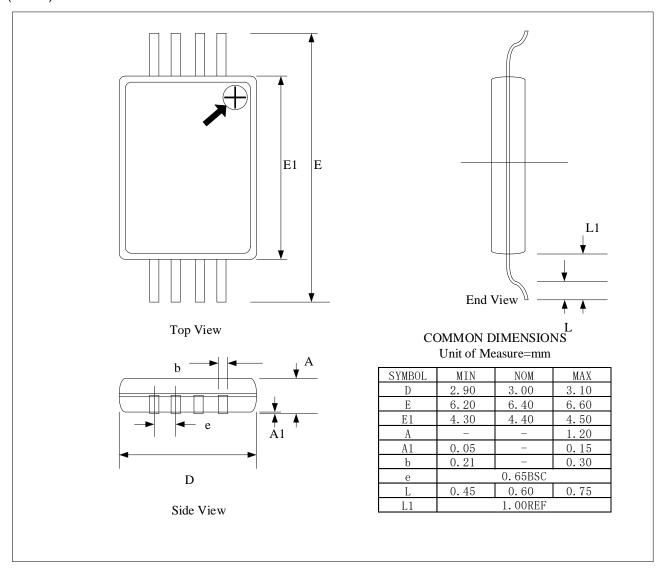
(256×8)Package Information SOP





24C01/24C02 2K bits

(256×8)**TSSOP**

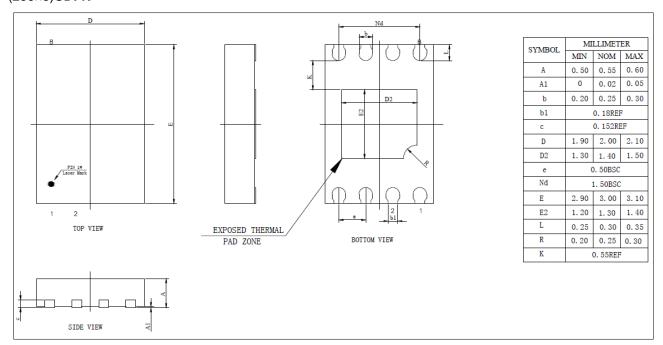


24C01/24C02 15/ 19



24C01/24C02 2K bits

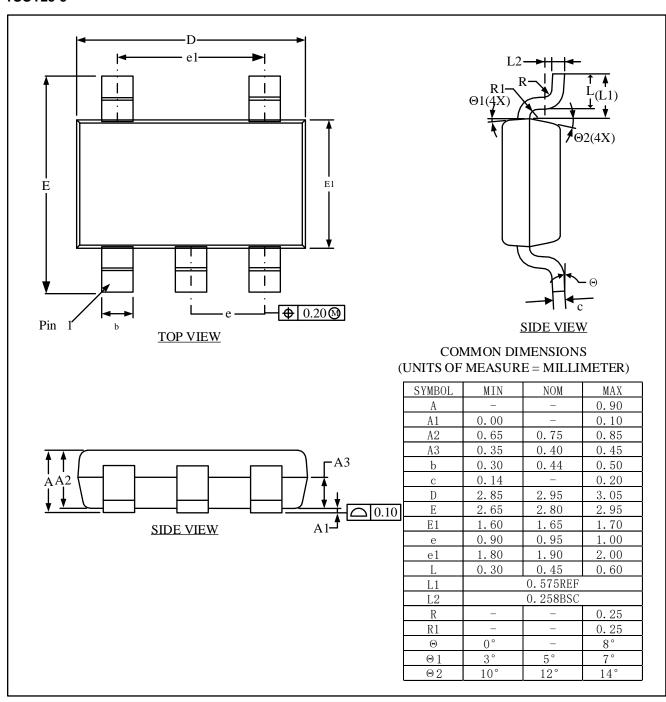
(256×8)UDFN



24C01/24C02 16/ 19



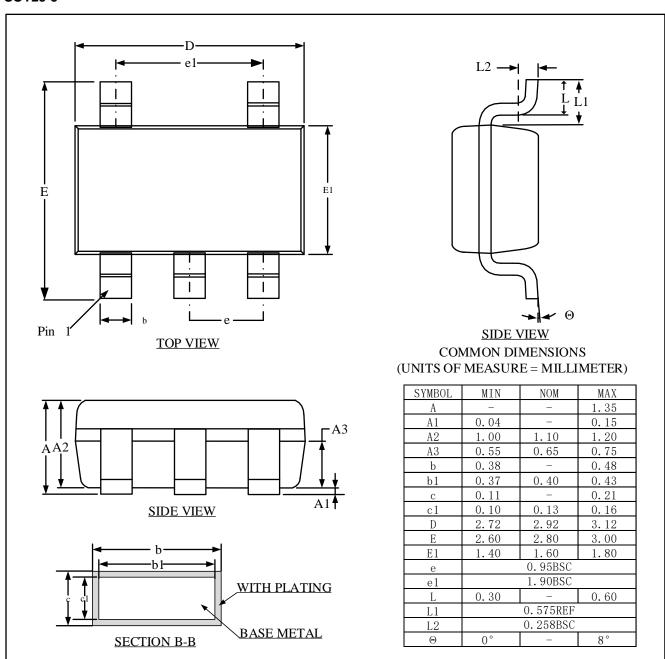
TSOT23-5



24C01/24C02 17/ 19



SOT23-5



重要通知与免责声明

深圳市钍地半导体有限公司将准确可靠地提供技术和可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、WEB工具、安全信息和其他资源,但不保证任何缺陷,一切以实物测试为准,并且不作任何明示或暗示的保证,包括但不限于对适销性的暗示保证、对特定目的适用的暗示保证或不侵犯任何第三方知识产权的暗示保证。

这些资源旨在为使用钍地产品的熟练开发人员提供支持:(1)为您的应用程序选择合适的产品;(2)设计、验证和测试您的应用程序;(3)确保您的应用程序符合适用的标准和任何其他安全、安保或其他要求;(4)钍地和钍地标志是钍地半导体的注册商标。所有商标均为其各自所有者的财产;(5)有关更改详情,请查阅任何修订文件中包含的修订历史记录。资源可能会在不通知的情况下更改。我公司将不对使用此产品及其使用而导致的专利或第三方知识产权的侵权负责。

24C01/24C02



24C01/24C02 2K bits

(256×8) Revision

history

重要通知与免责声明

深圳市钍地半导体有限公司将准确可靠地提供技术和可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、WEB工具、安全信息和其他资源,但不保证任何缺陷,一切以实物测试为准,并且不作任何明示或暗示的保证,包括但不限于对适销性的暗示保证、对特定目的适用的暗示保证或不侵犯任何第三方知识产权的暗示保证。 这些资源旨在为使用钍地产品的熟练开发人员提供支持:(1)为您的应用程序选择合适的产品;

这些资源旨在为使用钍地产品的熟练开发人员提供支持:(1)为您的应用程序选择合适的产品;(2)设计、验证和测试您的应用程序;(3)确保您的应用程序符合适用的标准和任何其他安全、安保或其他要求;(4)钍地和钍地标志是钍地半导体的注册商标。所有商标均为其各自所有者的财产;(5)有关更改详情,请查阅任何修订文件中包含的修订历史记录。资源可能会在不通知的情况下更改。我公司将不对使用此产品及其使用而导致的专利或第三方知识产权的侵权负责。

24C01/24C02